



100V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
-100V	4.2Ω @ V _{GS} = -10V	-0.27A
-1007	5.0Ω @ V _{GS} = -4.0V	-0.24A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- · Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.







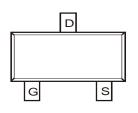
Top View

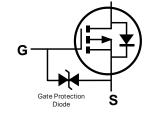
Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
 ESD Protected up to 2KV (HBM)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)





Top View Pin Configuration

Equivalent Circuit

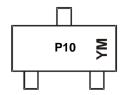
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP10H4D2S-7	SOT23	3,000/Tape & Reel
DMP10H4D2S-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



P10 = Product Type Marking Code YM = Date Code Marking Y or \(\overline{Y} = Year (ex: E = 2017) \) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	Е		F	G		Н			J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-100	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	-0.27 -0.21	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle ≤1%)	I _{DM}	-1.0	Α		
Maximum Body Diode Continuous Current (Note 6)			Is	-0.42	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Dawer Discinction		(Note 5)	0	0.38	W
Total Power Dissipation		(Note 6)) P _D	0.44	VV
Thermal Resistance, Junction to Ambient	ent Steady		$R_{ heta JA}$	333	
Thermal Resistance, Junction to Ambient State		(Note 6)	$R_{ heta JA}$	282	°C/W
Thermal Resistance, Junction to Case		(Note 6)	$R_{ heta JC}$	115	
Operating and Storage Temperature Range			$T_{J_i}T_{STG}$	-55 to +150	°C

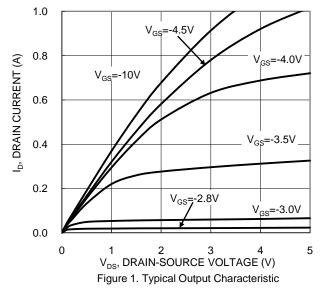
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-100	—	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	1	μΑ	$V_{DS} = -100V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	-2.3	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	2.8	4.2	Ω	$V_{GS} = -10V, I_D = -0.5A$	
Static Brain-Source On-Resistance	R _{DS(ON)}		3.2	5.0	32	$V_{GS} = -4.0V, I_D = -0.1A$	
Diode Forward Voltage	V_{SD}		-0.82	-1.3	V	$V_{GS} = 0V, I_{S} = -0.2A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	87			V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	5.6	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	2.9				
Gate Resistance	R _G	_	15.3	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Qg	_	1.8	_			
Gate-Source Charge	Q _{gs}	_	0.3	_	nC	$V_{DS} = -80V, V_{GS} = -10V,$ $I_{D} = -0.5A$	
Gate-Drain Charge	Q_{gd}	_	0.5	_		ID = -0.5A	
Turn-On Delay Time	t _{D(ON)}	_	3.3	_			
Turn-On Rise Time	t _R	_	2.6	_	no	$V_{DS} = -50V, I_{D} = -0.5A,$	
Turn-Off Delay Time	t _{D(OFF)}		8.4	_	ns	$V_{GS} = -10V$, $R_G = 10\Omega$	
Turn-Off Fall Time	t _F	—	4.9	_			
Reverse Recovery Time	t _{RR}		17.8	_	ns	V _R = -100V, I _F = -1.0A,	
Reverse Recovery Charge	Q _{RR}	_	24.8	_	nC	di/dt = 100A/µs	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- Device mounted on FR-4 substrate PC board, 202 copper, with 1inch square copper pad layout.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.





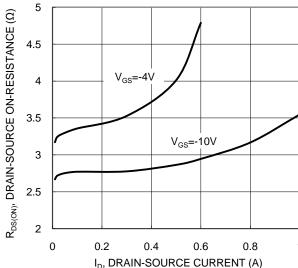


Figure 3. Typical On-Resistance vs. Drain Current and

Gate Voltage

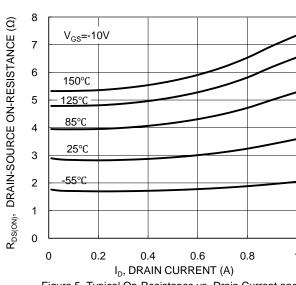
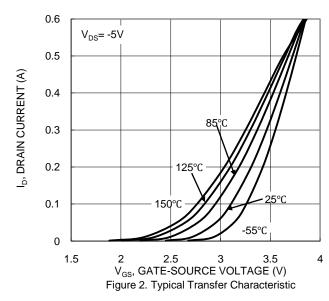
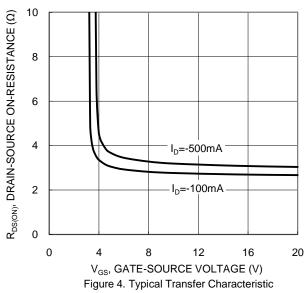


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





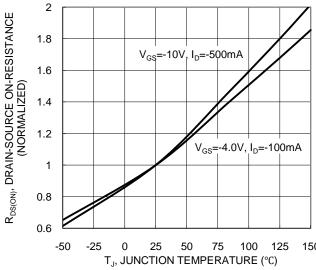
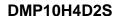
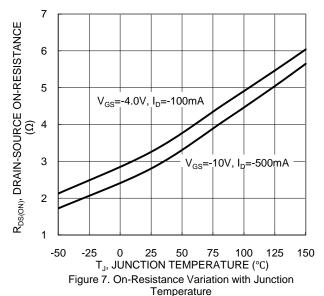


Figure 6. On-Resistance Variation with Junction Temperature







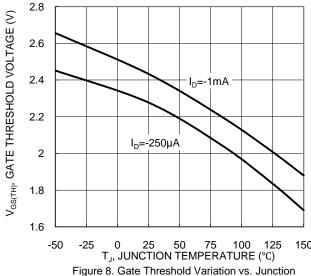
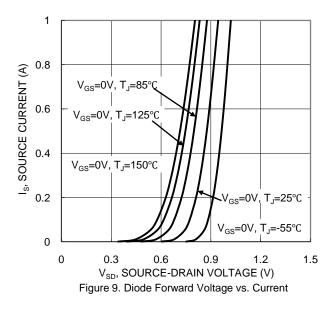
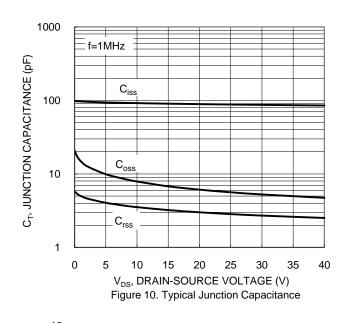
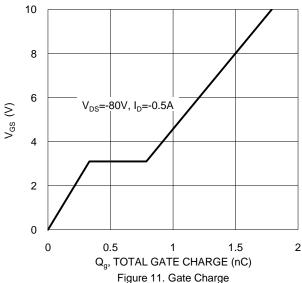
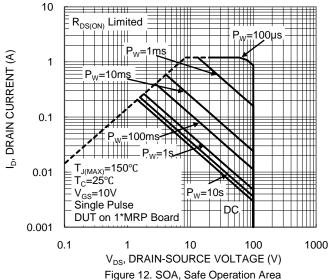


Figure 8. Gate Threshold Variation vs. Junction Temperature

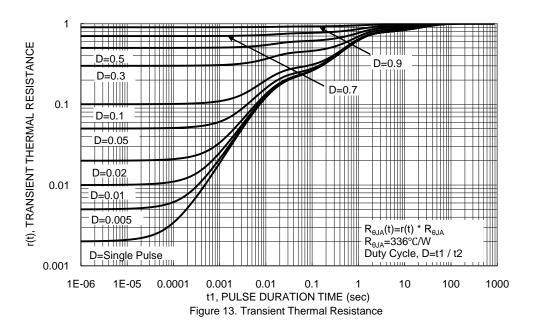








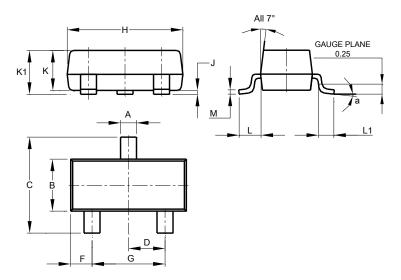




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



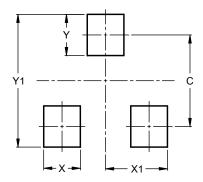
SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

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